Arnout Beckers

List of Publications by Year
in descending order

14 papers	697 citations	1307594 7 h-index	1588992 8 g-index
14 all docs	14 docs citations	14 times ranked	406 citing authors

#	Article	IF	Citations
1	Generalized Boltzmann relations in semiconductors including band tails. Journal of Applied Physics, 2021, 129, .	2.5	9
2	Theoretical Limit of Low Temperature Subthreshold Swing in Field-Effect Transistors. IEEE Electron Device Letters, 2020, 41, 276-279.	3.9	108
3	Physical Model of Low-Temperature to Cryogenic Threshold Voltage in MOSFETs. IEEE Journal of the Electron Devices Society, 2020, 8, 780-788.	2.1	51
4	Inflection Phenomenon in Cryogenic MOSFET Behavior. IEEE Transactions on Electron Devices, 2020, 67, 1357-1360.	3.0	26
5	Cryo-CMOS Compact Modeling. , 2020, , .		15
6	A Review on Quantum Computing: From Qubits to Front-end Electronics and Cryogenic MOSFET Physics. , 2019, , .		57
7	Characterization and modeling of 28-nm FDSOI CMOS technology down to cryogenic temperatures. Solid-State Electronics, 2019, 159, 106-115.	1.4	76
8	Cryogenic MOSFET Threshold Voltage Model. , 2019, , .		35
9	Characterization and Modeling of 28-nm Bulk CMOS Technology Down to 4.2 K. IEEE Journal of the Electron Devices Society, 2018, 6, 1007-1018.	2.1	107
10	28-nm Bulk and FDSOI Cryogenic MOSFET : (Invited Paper). , 2018, , .		1
11	Energy filtering in silicon nanowires and nanosheets using a geometric superlattice and its use for steep-slope transistors. Journal of Applied Physics, 2018, 124, .	2.5	5
12	Design-oriented modeling of 28 nm FDSOI CMOS technology down to 4.2 K for quantum computing. , 2018, , .		32
13	Cryogenic MOS Transistor Model. IEEE Transactions on Electron Devices, 2018, 65, 3617-3625.	3.0	114
14	Cryogenic characterization of 28 nm bulk CMOS technology for quantum computing. , 2017, , .		61